

Notice of Allowability	Application No.	Applicant(s)	
	10/748,308	WON ET AL.	
	Examiner	Art Unit	
	Thinh T. Nguyen	2818	
The MAILING DATE of this communication appeal claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT ROOF the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate commu IGHTS. This application is so	this application. If not included nication will be mailed in due course. THIS	ve
1. This communication is responsive to <u>10/14/2005</u> .			
2. 🔀 The allowed claim(s) is/are <u>8-22</u> .			
3.  Acknowledgment is made of a claim for foreign priority una)  All b)  Some* c)  None of the:  1.  Certified copies of the priority documents have 2.  Certified copies of the priority documents have 3.  Copies of the certified copies of the priority do International Bureau (PCT Rule 17.2(a)).  * Certified copies not received:  Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.  4.  A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give 5.  CORRECTED DRAWINGS (as "replacement sheets") must (a)  including changes required by the Notice of Draftspers	e been received. e been received in Application cuments have been received of this communication to file MENT of this application.  iitted. Note the attached EXA es reason(s) why the oath or	in No in this national stage application from the a reply complying with the requirements  MINER'S AMENDMENT or NOTICE OF declaration is deficient.	
1)  hereto or 2)  to Paper No./Mail Date	=	(170 040) attached	
(b) including changes required by the attached Examiner's Paper No./Mail Date  Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in to the sheet of the sheet	s Amendment / Comment or .84(c)) should be written on th he header according to 37 CFI	e drawings in the front (not the back) of R 1.121(d).	
attached Examiner's comment regarding REQUIREMENT			
Attachment(s) 1. ☐ Notice of References Cited (PTO-892)	5.  Notice of Inf	ormal Patent Application (PTO-152)	
2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)	6. ☐ Interview Su	mmary (PTO-413),	
3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0		Mail Date Amendment/Comment	
Paper No./Mail Date 4.	8. 🛭 Examiner's 9. 🔲 Other	Statement of Reasons for Allowance	
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Fechnology Center 2800			

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## **DETAILED ACTION**

### Restriction /election.

1. Applicant election of claims 8-22 for prosecution without traverse in the communication with the Office on 10/14/2005 is acknowledged.

# Examiner's Amendment.

2. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee:

A/ Cancels non-elected Claims 23-29.

B/ Changes the title to:

-- METHOD FOR MANUFACTURING CAPACITOR OF SEMICONDUCTOR DEVICE --

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#### Reason for allowance

3. The following is an examiner's statement of reason for allowance: None of the references of record teaches or suggests the claimed METHOD FOR MANUFACTURING

**CAPACITOR OF SEMICONDUCTOR DEVICE** having the limitations:

-- " forming a capacitor lower electrode on a semiconductor substrate; forming a multilayer structure over the capacitor lower –electrode wherein forming the multi-layer structure comprises:

forming a first dielectric layer comprising aluminum oxide on the capacitor lower electrode atomic laver deposition (ALD) using an O2 plasma; forming a second dielectric layer comprising a material having a higher dielectric constant than aluminum oxide on the first dielectric layer by ALD using O2 Plasma; forming a third dielectric layer comprising aluminum oxide on the second dielectric layer by ALD using the O2 plasma; and forming a capacitor upper electrode on the third dielectric layer. "--

and all other limitations as recited in claim 1.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance".

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### Conclusion

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thinh T Nguyen whose telephone number is 703-305-0421. The examiner can normally be reached on Monday-Friday 8:30am-5: 00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on 703-308-4910. The fax phone numbers for the organization where this application or proceeding is assigned is 571-273-1790.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval [ PAIR ] system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Thinh T Nguyen TTV

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David Neims Supervisory Patent Examiner Technology Center 2800 Page 4